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Positron trapping kinetics in thermally generated vacancy donor complexes in highly As-doped silicon

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We have measured positron lifetime and Doppler broadening in highly As-doped silicon containing thermally generated V-As3 defect complexes (vacancy is surrounded by three arsenic atoms). We observe positron detrapping from the V-As3 defect complex and determine the binding energy of 0.27 eV of a positron to the complex. The results explain why 85% of the thermal vacancies formed in highly As-doped Si at temperatures over 700 K are invisible to positron measurements at elevated temperatures.

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I. INTRODUCTION

Miniaturization of field-effect transistors requires higher and higher doping densities to maintain a sufficient conductance of the source and drain areas. In the case of arsenic, problems arise when the donor concentration is increased above \( \sim 3 \times 10^{20} \) cm\(^{-3} \). At doping levels this high, the free electron concentration stops increasing linearly with the doping density and saturates. At the same time, a new As-donor concentration stops increasing linearly with the doping density and saturates.2,3 At the same time, a new As-donor concentration stops increasing linearly with the doping density and saturates. At the same time, a new As-donor concentration stops increasing linearly with the doping density and saturates.4

Thermal vacancies that form during processes at high temperatures can mediate the diffusion of impurity atoms in silicon. This diffusion leads to the formation of electrically passive donor impurity clusters, thus playing a significant role in electrical deactivation of the material. Recently, thermal vacancies have been directly observed with the positron annihilation spectroscopy in highly n-type silicon.3

Positron annihilation spectroscopy is suitable for observing thermal vacancies directly at high temperatures where they form. In intrinsic silicon, the concentration of thermal vacancies is still below the detection limit of positron measurements (\( \sim 10^{16} \) cm\(^{-3} \)) even at 1600 K.6,7 However, in highly n-type Si thermal vacancies form more abundantly as pairs with donor atoms and in negative charge state due to electron trapping, which both lower the formation energy.3

Measurements carried out in P-doped Si show the increase in positron lifetime as the thermal vacancies diffuse from the surface (where they form) into the bulk.5 In highly As-doped Si, however, the effect is greatly reduced, since most of the thermally generated vacancies (\( \sim 85\% \)) seem to be invisible as far as positron measurements are concerned.3

In this work we show that this is due to positrons escaping from vacancy-impurity complexes at high temperatures and determine the binding energy of 0.27(3) eV of a positron to the V-As3 complex.

II. METHOD

A. Experimental details

Our samples were Czochralski-grown Si(111) bulk crystals with an As doping of \( 1 \times 10^{20} \) cm\(^{-3} \). The untreated sample (1) contained a small concentration (\( \sim 10^{17} \) cm\(^{-3} \)) of native V-As3 defects, as shown in Ref. 9. The samples 3 and 4 have been annealed at 900 and 920 K until the thermal equilibrium vacancy concentration has been achieved and then quenched to room temperature, as reported in Ref. 5.

The positron lifetime experiments were carried out using a conventional fast-fast lifetime spectrometer with a time resolution of 260 ps and a \(^{22}\)NaCl source with a positron activity of 10 \( \mu \)Ci. The positron annihilations in the source material, in the Ni-foil covering the source, and as positronium were determined using a reference sample and subtracted from the lifetime spectra before the analysis. The sample temperature during the measurements was controlled by liquid nitrogen cooling and resistive heating systems.

The lifetime spectra \( n(t) = \Sigma f_i \exp(-t/\tau_i) \) were analyzed as a sum of exponential decay components convoluted with the Gaussian resolution function of the spectrometer. The indexes \( i \) correspond to the different lifetime components in the spectra with individual lifetimes \( \tau_i \) and intensities \( f_i \). The increase of the average lifetime \( \tau_{avr} \) above the bulk lifetime \( \tau_B = 218 \) ps in Si is an indication of vacancies being present in the material.10 This parameter coincides with the center of

<table>
<thead>
<tr>
<th>Sample</th>
<th>( T ) (K)</th>
<th>( t ) (h)</th>
<th>( \tau_{avr} ) at RT (ps)</th>
<th>([V] ) (10(^{19} ) cm(^{-3} ))</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>700</td>
<td>25</td>
<td>226</td>
<td>0.4(1)</td>
</tr>
<tr>
<td>2</td>
<td>750</td>
<td>188</td>
<td>800 88</td>
<td>234</td>
</tr>
<tr>
<td>3</td>
<td>900</td>
<td>17</td>
<td>243</td>
<td>5.2(5)</td>
</tr>
<tr>
<td>4</td>
<td>920</td>
<td>168</td>
<td>243</td>
<td>5.2(5)</td>
</tr>
</tbody>
</table>
mass of the lifetime spectrum and is insensitive to the decomposition process. Changes even as low as 1 ps can be reliably measured. The vacancy concentrations were determined from the average positron lifetime using the conventional positron trapping model with a trapping coefficient of $\mu_D = 2 \times 10^{15}$ s$^{-1}$.

The Doppler broadening of the annihilation radiation was measured simultaneously with positron lifetime using a Ge detector with an energy resolution of 1.3 keV at 511 keV. The Doppler broadened momentum distribution was analyzed using the conventional shape parameters $S$ and $W$, which describe the positron annihilation fraction with low momentum electrons ($|p_z| < 3 \times 10^{-3} m_0 c$) and with high momentum electrons ($9 \times 10^{-3} m_0 c < |p_z| < 15 \times 10^{-3} m_0 c$), respectively. The Doppler technique gives information not only on the vacancy concentration, but also about chemical surroundings of the vacancy.

### B. Positron trapping at defects

The positron annihilation rate $\lambda_i$ in a state $i$ is proportional to the electron density at the site of the positron. Each state has thus a characteristic lifetime $\tau_i$ defined as $\tau_i = 1/\lambda_i$. The experimental positron lifetime spectrum can be decomposed into several lifetime components allowing the determination of the fractions of positrons annihilating in various states. The average lifetime, when $N$ lifetime components can be separated from the experimental spectrum, is

$$\tau_{\text{ave}} = \sum_{j=1}^{N} I_j \tau_j,$$  \hspace{1cm} (1)

where $I_j$ is the intensity of the lifetime component. In the common case of one type of defect with a specific lifetime $\tau_D$ and no detrapping, the higher lifetime component $\tau_2 = \tau_D$ gives directly the defect lifetime and the smaller lifetime component is the modified bulk lifetime$^{12}$ $\tau_1 = (\tau_D^1 + \kappa_D)^{-1}$.

The lifetime components change, however, if the positrons escape from the trap. In the case of one type of defect and taking into account the detrapping, the lifetime components $\tau_1$ and $\tau_2$ depend on the trapping parameters as$^{12}$

$$\frac{1}{\tau_{1,2}} = \frac{1}{2} \left( \frac{\tau_D^1 + \tau_D^1 + \kappa + \delta \pm \sqrt{(\tau_D^1 + \kappa - \tau_D^1 - \delta)^2 + 4 \kappa \delta}}{\tau_D^1 + \kappa - \delta} \right)^{1/2}.$$  \hspace{1cm} (2)

The escape rate $\delta$ at a temperature $T$ is given by$^{13}$

$$\delta = \mu_D \left( \frac{2 \pi m^* k_B T}{\hbar^2} \right) \exp \left( - \frac{E_b}{k_B T} \right),$$  \hspace{1cm} (3)

where $E_b$ is the binding energy of the positron to the trap and $m^*$ is the effective mass of the positron ($m^* = m_0$). The trapping rate of positrons to the vacancies $\kappa$ is proportional to the defect concentration $c_D$ (Ref. 10)

$$\kappa = \mu_D c_D,$$  \hspace{1cm} (4)

where $\mu_D$ is the trapping coefficient.

Finally, the intensities in Eq. (1) are given by$^{12}$

$$I_1 = \frac{\lambda_1 - \lambda_2}{\lambda_1 - \lambda_2} \quad \text{and} \quad I_2 = \frac{\tau_2}{\tau_1 \tau_2 - \tau_1}.$$  \hspace{1cm} (5)

$$I_2 = \frac{\tau_2}{\tau_1 \tau_2 - \tau_1}.$$  \hspace{1cm} (6)

### III. RESULTS

#### A. Lifetime measurements during annealing

The average positron lifetime measured at room temperature in the untreated sample 2 (the same as 1) before annealings was $\tau_{\text{ave}} = 226$ ps. When the temperature during the positron measurements was increased to 700 K the average positron lifetime decreased to $\tau_{\text{ave}} \approx 220$ ps. Figure 1 shows the average positron lifetime as a function of isothermal annealing time at temperatures 700, 750, and 800 K. The measurements were carried out in situ at the annealing temperatures. The positron lifetime starts to increase already at 700 K. During 180 h at 750 K, the average positron lifetime increases to the value of $\tau_{\text{ave}} \approx 224$ ps. At 800 K the curve shows signs of saturation to about 225 ps.

Interestingly, after the long annealing at 800 K, the average positron lifetime after cooling down to room temperature increased to a value of $\tau_{\text{ave}} \approx 234$ ps. This lifetime is much larger than that observed during the 800 K annealing and suggests that only a small fraction of the vacancy defects trap positrons at 750 and 800 K. The samples annealed at 900 and 920 K (3 and 4) were measured only after cooling down.

#### B. Lifetime measurements after annealing

In order to understand what causes the increase in the average positron lifetime after cooling down from the an-
nealing temperature, we measured the positron lifetime in the temperature range from 180 to 700 K after completing the isothermal annealing experiments. The results are shown in Fig. 2. The four samples have different thermal histories and thus different vacancy concentrations, which increase the average positron lifetime from the bulk value at room temperature.

The average positron lifetime remains constant up until 400 K, at which temperature it starts decreasing. The decrease continues up to 700 K, where the lifetime in the samples 1 and 2 shows signs of saturation. The decrease is visible in all the measured samples and it is much stronger than the normal temperature dependence ($T^{-1/2}$) of the trapping coefficient for negatively charged defects at these temperatures.$^{14}$ This behavior is reversible with temperature, which cancels out the possibility of defects annealing out.

The higher lifetime component $\tau_2$ also presented in Fig. 2 shows decreasing behavior in the two samples with smaller vacancy concentration. This can be explained by positrons escaping from the defect at high temperatures. The higher lifetime component in the samples annealed at 900 and 920 K does not decrease with temperature. In the sample annealed at 900 K, $\tau_2$ remains constant whereas in the 920 K annealed sample $\tau_2$ even increases. This can be explained by trapping of positrons to an additional defect in these two samples.

C. Doppler broadening results

The $S$ and $W$ parameters measured in the samples as a function of temperature are presented in Fig. 3. The parameters have been scaled to the values in the bulk.
ever, after the long annealing at 750 and 800 K, positron measurements at temperatures above 700 K. How-

terestingly, the average positron lifetime is much lower at 700 K than at room temperature both before and after the

annealing at high temperature. This indicates that only a small fraction (∼15%) of thermal vacancies is visible to

positron measurements at temperatures above 700 K. However, after the long annealing at 750 and 800 K (Fig. 1) the

V-As3 concentration increased from $4 \times 10^{17}$ to $1 \times 10^{18}$ cm$^{-3}$ showing that, although invisible at high temperature, thermal vacancies form abundantly and remain in vacancy impurity complexes after cooling down.

The fit to the lifetime data measured at 750 K has been calculated from the fits to the lifetime data using

$$P = \frac{\tau_{ave} - \tau_B}{\tau_D - \tau_B} (P_D - 1) + 1,$$

where the parameter $P$ corresponds to the shape parameters $S$ and $W$ and $P_D$ the parameter values in the defect state (scaled to the bulk value of 1). The calculated curves show that the Doppler results are in good agreement with the lifetime data.

IV. DISCUSSION

The increase in the average positron lifetime in Fig. 1 is due to thermal vacancies diffusing from the surface into the bulk Si similarly as observed previously in P-doped Si. Interestingly, the average positron lifetime is much lower at 700 K than at room temperature both before and after the annealings at high temperature. This indicates that only a small fraction (∼15%) of thermal vacancies is visible to positron measurements at temperatures above 700 K. However, after the long annealing at 750 and 800 K (Fig. 1) the V-As3 concentration increased from $4 \times 10^{17}$ to $1 \times 10^{18}$ cm$^{-3}$ showing that, although invisible at high temperature, thermal vacancies form abundantly and remain in vacancy impurity complexes after cooling down.

The fit to the lifetime data measured at 750 K has been obtained using the diffusion equation assuming vacancy formation at the surface followed by migration into the bulk. The formation entropy was fixed to the value of $5k_B$ similarly as in Ref. 5 and the defect lifetime was assumed to be 248 ps, which corresponds the positron lifetime in the As-decorated Si monovacancy. The fit gives a formation energy $E_f$ = 0.8(2) eV and a migration energy $E_m$ = 1.5(1) eV. These values are comparable to those obtained earlier in P-doped Si. The migration energy appears to be slightly larger in As-doped Si, which reflects the lower diffusivity of vacancies in As-doped than in P-doped Si.

We fitted the average lifetime data presented in Fig. 2 using the kinetic trapping model [Eqs. (1)–(5)]. Using the defect lifetime of $\tau_D$ = 248 ps (average at 180–350 K) and the bulk lifetime $\tau_B$ = 218 ps, the fit gives a binding energy of $0.27(3)$ eV and defect concentrations of $4 \times 10^{17}$, $1 \times 10^{18}$, $5 \times 10^{18}$, and $5 \times 10^{18}$ cm$^{-3}$ for the untreated sample (1) and samples annealed at 800, 900 and 920 K (2, 3, and 4), respectively.

The solid and dashed curves in the lower part of Fig. 2 have been calculated from the fits to the average lifetime data and demonstrate that in the samples 1 and 2 the higher lifetime component decreases as expected assuming positrons escape the trap. However, in the samples annealed at 900 and 920 K the higher lifetime component (Fig. 2) does not decrease as expected in the case of detrapping. In these samples the defect concentration is close to $10^{19}$ cm$^{-3}$, which suggests that the vacancy concentration approaches the limit where all the As atoms are part of V-As3 complexes, the doping concentration being $\sim 10^{20}$ cm$^{-3}$. The V-As3 complex is formed when a diffusing V-As3 complex meets yet another As atom. When the V-As3 concentration approaches the concentration of free As atoms, the diffusing V-As3 is as likely to find a ready-made V-As3 complex as a separate As atom and form a V2-As5 complex. Similar defect complexes have been reported in highly As doped silicon earlier and it has been confirmed that the relative amount of V2-As5 increases dramatically during annealings at 800 °C. This is consistent with the fact that the effect of V2-As5 shows in the two samples with the highest annealing temperatures.

The V2-As5 complexes are not observed at room temperature because the V-As3 dominate, but as the positrons escape from V-As3 above 400 K, they may still trap into V2-As5. However, as the overall trapping at vacancy defects still decreases, $\tau_{ave}$ decreases with temperature similarly as in the case of the samples annealed at lower temperatures. The characteristic positron lifetime at V2-As5 is likely to be close to the lifetime in an undecorated Si divacancy, about 290 ps, or slightly lower due to the As-decoration. From the fact that $\tau_2$ is highest in sample 4, it can be concluded that the concentration of V2-As5 is highest in this sample that has been annealed the longest time in the highest temperature. In the V2-As5 complex the $S$ parameter is higher and the $W$ parameter lower than in the case of V-As3, explaining why the $S$ parameter increases and the $W$ parameter decreases with increasing temperature more rapidly than expected from the lifetime data in samples 3 and 4 (see curves in Fig. 3).

The positron trapping at V-As3 can be compared with the results obtained from the vacancy-impurity complexes in P-doped Si. Specifically the results in Fig. 1 can be compared with similar data from the P-doped samples. In both cases the average positron lifetime increases as a function of measurement time as the vacancies diffuse from the surface into the bulk of the sample. However, the effect is much larger in magnitude in P-doped Si. This indicates that the positrons do not escape from the V-P3 complex at these temperatures. This is in agreement with the earlier results from positron measurements in P-doped Si. As positrons escape efficiently from the V-As3 at high temperatures, the vacancy defects observed during the annealing at high temperatures are therefore monovacancies decorated with only one or two As atoms and divacancies decorated with As atoms such as the V2-As5 complex.
V. CONCLUSIONS

We have carried out positron lifetime and Doppler broadening experiments in highly As-doped silicon containing thermally generated V-As$_3$ complexes. We observed thermal escape of positrons from the V-As$_3$ complex at high temperatures. The detrapping starts at 400 K and from the temperature dependence of the positron lifetime we determine the binding energy of positrons to V-As$_3$ as 0.27(3) eV. The formation of V-As$_3$ complexes from diffusing thermal vacancies and subsequent detrapping of positrons from the V-As$_3$ complex explains why the increase in the average positron lifetime due to thermal vacancies is clearly smaller in As-doped Si than in P-doped Si at high temperatures, in spite of the similarity of the vacancy formation energies in the two materials.

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